



**HIGH ELECTRON CONCENTRATION WAFERS**

**n-type**

<b>TECHNICAL SPECIFICATION</b>		
<b>Features</b>	<b>Units</b>	<b>Available planes</b>
		<b>C-plane (0001)</b>
<b>Carrier concentraton</b>	cm <sup>-3</sup>	~10 <sup>19</sup>
<b>Dopant</b>		Oxygen
<b>Resistvity</b>	Ωcm	~10 <sup>-3</sup>
<b>Mobility</b>	cm <sup>2</sup> / Vs	~150
<b>Thickness</b>	μm	350 ±50
<b>TTV</b>	μm	≤40
<b>Bow</b>	μm	≤10
<b>FWHM (0002) of XRC, (epi-ready; 0.1x0.1 mm slit)</b>	arcsec	~20
<b>Etch Pits Density (EPD)</b>	cm <sup>-2</sup>	~5x10 <sup>4</sup>
<b>Off-cut</b>	deg	0.3±0.1 to the m-direction
<b>Surface fnishing</b>	Front side	epi-ready (RMS < 0.5 nm)
	Back side	rough
<b>Available sizes</b>		10x10mm 1-inch 1.5-inch
<b>Packaging</b>		separate single wafer container
<b>Special request</b>		for pricing or technical enquiries please contact our sales team

